

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,828,235 B2
DATED : December 7, 2004
INVENTOR(S) : Satoshi Takano

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

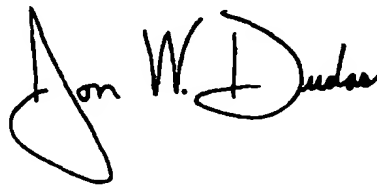
Column 17.

Line 45, claim 9 should read as follows:

9. A substrate processing method, comprising
- a first step of carrying a substrate into a preliminary chamber from an external part;
 - a second step of continuously supplying and exhausting an inert gas to and from said preliminary chamber at least from a time before opening a first gate between said preliminary chamber and a transfer chamber, after the substrate is carried into said preliminary chamber;
 - a third step of transferring said substrate to said transfer chamber from said preliminary chamber, in a state in which the inert gas is continuously supplied and exhausted to and from said preliminary chamber and said transfer chamber, after said first gate valve is opened;
 - a fourth step of transferring said substrate to a process chamber from said transfer chamber in a state in which the inert gas is continuously supplied and exhausted to and from said transfer chamber and said process chamber, after a second gate valve between said transfer chamber and said process chamber is opened; and
 - a fifth step of subjecting said substrate to predetermine processing in said process chamber.

Signed and Sealed this

Fourteenth Day of June, 2005

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office